

BAL 1115: 1600nm / 0.5W Broad Area Laser Diode Chip

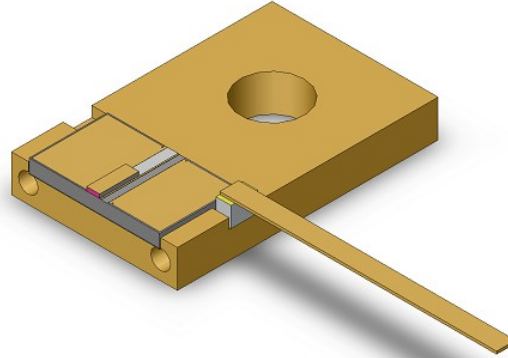
7.1.2.SP.1115 Rev B

Preliminary Model

Description

COVEGA's broad area laser diode is based on a highly efficient InP/InGaAsP Quantum Well (QW) layer structure.

Advanced MBE epitaxial wafer growth techniques and die bonding processes enable reliable high-power laser diode operation.



Applications

- ✓ Medical
- ✓ Industrial
- ✓ Source Laser for Free Space Optical
Wireless Communication

Features

- High Optical Output Power
- High Slope Efficiency
- Numerous Packaging Options

Specifications

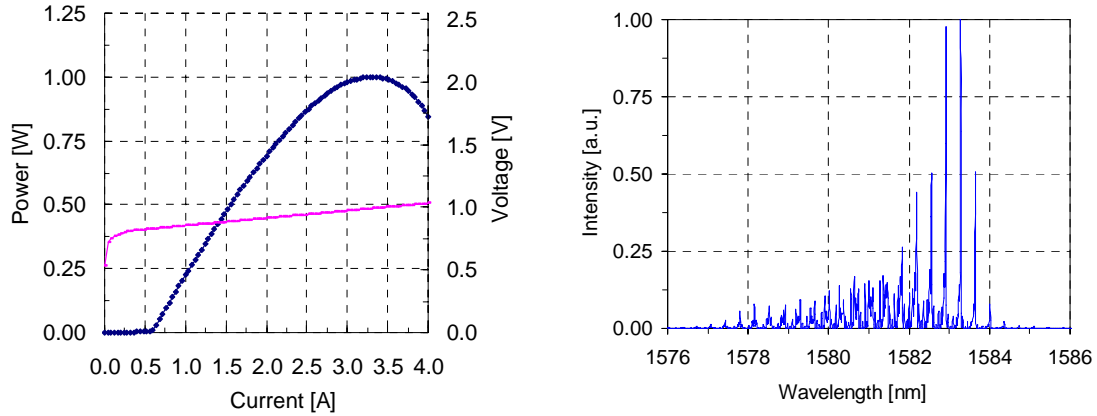
CW, T (Chip) = 25°C

Parameter		Min	Typ	Max	
Operating Current	I_{OP}		1.7	2.2	A
Center Wavelength	λ_C	1580	1600	1620	nm
Spectral Bandwidth (rms)	$\Delta\lambda$		7	14	nm
Output Power over C-Band	P_{OUT}	0.5			W
Threshold Current	I_{TH}		0.5	0.8	A
Slope Efficiency	$\Delta P/\Delta I$	0.3	0.4		W/A
Forward Voltage	V		3	4	V
Chip Length	L		0.6		mm
Emitter Width	W		100		μm
Beam Divergence Angle (FWHM)					
- Transverse	θ_T		28	36	deg
- Lateral	θ_L		8	14	deg

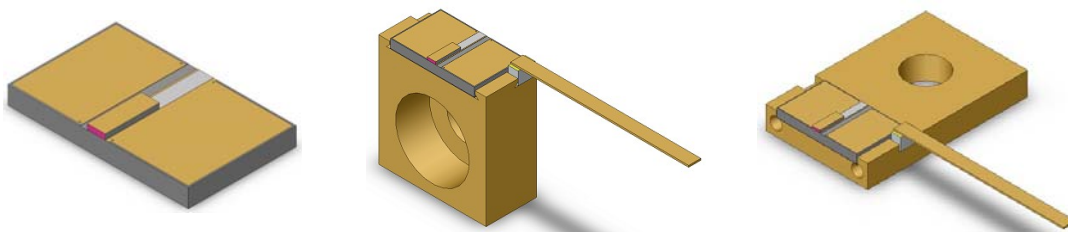
SPECIFICATIONS SUBJECT TO CHANGE WITHOUT NOTICE

BAL 1115

Performance



Packaging



Chip on Submount

C-Mount

CT-Mount

Ordering Information

BAL 1115 - XXX	
XXX	
Submount	
COS = Chip on submount	
CMN = C-Mount	
CTM = CT-Mount	
ZZZ = Custom Mount	

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